

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,849,901 B2  
DATED : February 1, 2005  
INVENTOR(S) : Falster

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

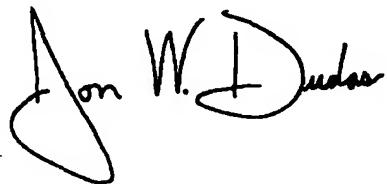
Title page

Item [54], Title, should read:

**-- SILICON-ON-INSULATOR STRUCTURE HAVING A DEVICE LAYER  
WHICH IS VACANCY DOMINATED AND SUBSTANTIALLY FREE OF  
AGGLOMERATED VACANCY-TYPE DEFECTS --**

Signed and Sealed this

Thirteenth Day of December, 2005



JON W. DUDAS  
*Director of the United States Patent and Trademark Office*